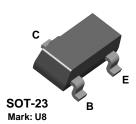


BSR14



NPN General Purpose Amplifier

This device is for use as a medium power amplifier and switch requiring collector currents up to 500 mA. Sourced from Process 19. See BCW65C for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	40	V	
V _{CBO}	Collector-Base Voltage	75	V	
V _{EBO}	Emitter-Base Voltage	6.0	V	
I _C	Collector Current - Continuous	800	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BSR14	
P _D	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

^{*}Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

NPN General Purpose Amplifier

(continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAF	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_C = 10 \ \mu\text{A}, \ I_B = 0$	75		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	40		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	6.0		V
Ісво	Collector-Cutoff Current	V _{CB} = 60 V V _{CB} = 60 V, T _A = 150°C		10 10	nA μA
I _{CEX}	Collector-Cutoff Current	V _{CE} = 60 V, V _{EB} = 3.0 V		10	nA
I _{BEX}	Reverse Base Current	V _{CE} = 60 V, V _{EB} = 3.0 V		20	nA
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$		15	nA
h _{FE}	ACTERISTICS DC Current Gain	$I_C = 0.1 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$	35 50		
I FE	DC Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}$	50 75 100	300	
.,	Oulle des Freites Out setting Valle	$I_C = 150 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V}$	50 40	0.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.3 1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.6	1.2 2.0	V V
SMALL SI	GNAL CHARACTERISTICS Current Gain - Bandwidth Product	I _C = 20 mA, V _{CE} = 20,	300		MHz
11		f = 100 mHz	000		1411 12
Ссв	Collector-Base Capacitance	V_{CB} = 10V, I_E = 0, f = 1.0 MHz		8.0	pF
h _{ie}	Input Impedance	V _{CE} =10V,I _C =1.0 mA,f=1.0 kHz	2.0	8.0	kΩ
h _{fe}	Small-Signal Current Gain	V _{CE} =10V,I _C =1.0 mA,f=1.0 kHz	50	300	
h _{oe}	Output Admittance	V _{CE} =10V,I _C =1.0 mA,f=1.0 kHz	5	35	μS
SWITCHIN	NG CHARACTERISTICS				
t _d	Delay Time	$V_{CC} = 30 \text{ V}, V_{BE(OFF)} = 0.5 \text{ V},$		10	ns
-u	Rise Time	$I_{\rm C} = 150 \text{ mA}, I_{\rm B1} = 15 \text{ mA}$		25	ns
-	Kise Tillie	, =:			
t _r	Storage Time	$V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA},$		225	ns

Spice Model

NPN (ls=14.34f Xti=3 Eg=1.11 Vaf=74.03 Bf=255.9 Ne=1.307 lse=14.34f lkf=.2847 Xtb=1.5 Br=6.092 Nc=2 lsc=0 lkr=0 Rc=1 Cjc=7.306p Mjc=.3416 Vjc=.75 Fc=.5 Cje=22.01p Mje=.377 Vje=.75 Tr=46.91n Tf=411.1p ltf=.6 Vtf=1.7 Xtf=3 Rb=10)

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